portions of the photoresist are then removed. This produces photoresist layers 198, 199 that are identical in appearance to the mask (Figure 12). Unlike the mask, however, the photoresist layer is not sensitive to an acidic solution used to etch the metal layer. Thus, dipping the structure in the acidic solution etches the metal layer where no photoresist film is present, but does not etch the film where photoresist film is present. The final product 200 (Figure 13) is a composite spacer layer with a total thickness comprised of the metal and the photoresist layer(s), and containing holes 210 etched therein and completely through the composite structure, the holes having the desired shape, size and pattern as desired as discussed above. Such composite spacer layer has very strong support due to the presence of the middle metal layer. The photoresist layers on both sides of the metal layer can provide insulation between the metal and the ITO-coated PET film.

REMARKS

By this Preliminary Amendment, specification paragraphs [0054] and [0059] are amended. The attached Appendix includes marked-up copies of each rewritten paragraph (37 C.F.R. §1.121(b)(1)(iii)).

No new matter is added by this Amendment, the amendments to these paragraphs being supported by paragraph [0059] of the original specification (page 11, lines 30-32) indicating that the photoresist is chemically altered at the exposed portions.

The change is required for technical accuracy of terminology in the art. In the processing of photoresists, ultraviolet light is used to chemically alter regions of the photoresist, e.g., to crosslink polymer chains to decrease solubility of the exposed area (negative photoresist) or to break polymer chains to increase solubility of the exposed areas (positive photoresist). The term "develop" generally refers to a process of washing the photoresist with a solvent after this exposure step in order to remove areas of the photoresist of high solubility. Thus, the term "develop" in paragraphs [0054] and [0059] of the original

specification was not fully accurate, and is corrected to eliminate this phrase and replace it with the "chemically alter" phrase also appearing in the original specification.

Prompt and favorable examination on the merits are earnestly solicited. Should the Examiner have any questions or comments, the Examiner is invited to contact Applicants' undersigned representative at the telephone number listed below.

Respectfully submitted,

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Date: January 16, 2002

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APPENDIX

Changes to Specification:

The following are marked-up versions of the amended paragraphs:

[0054] The etched photoresist spacer layer may be formed by first laminating the photoresist layer onto a conductive metal layer surface, i.e., the conductive metal layer of the bottom substrate, and masked. After exposure to, for example, ultraviolet light to chemically alter~~develop~~ the photoresist at exposed portions, the mask is removed and the photoresist is etched accordingly.

[0059] Once laminated, a mask 196 is placed upon a surface of one of the photoresist layers 192 as shown in Figure 11, the mask having a pattern such that it covers the area where etching is not desired. The structure is then exposed to, for example, ultraviolet light that chemically alters~~develops~~ the exposed portions of the photoresist films~~, i.e., it chemically alters these exposed portions of the photoresist layer~~. The exposed, developed portions of the photoresist are then removed. This produces photoresist layers 198, 199 that are identical in appearance to the mask (Figure 12). Unlike the mask, however, the photoresist layer is not sensitive to an acidic solution used to etch the metal layer. Thus, dipping the structure in the acidic solution etches the metal layer where no photoresist film is present, but does not etch the film where photoresist film is present. The final product 200 (Figure 13) is a composite spacer layer with a total thickness comprised of the metal and the photoresist layer(s), and containing holes 210 etched therein and completely through the composite structure, the holes having the desired shape, size and pattern as desired as discussed above. Such composite spacer layer has very strong support due to the presence of the middle metal layer. The photoresist layers on both sides of the metal layer can provide insulation between the metal and the ITO-coated PET film.